

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	93	(nonvolat\$4 adj3 (memory cell)) with first with second with (field adj effect adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 09:08
L2	65	1 and (gate-adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 09:04
L3	6550	257/257,316,319,321,324,326,315,311,322,326.ccls or 438/258,592,182,257-267,736,738,592.ccls. or 365/185.01,185.18ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 09:07
L4	9	3 and ((nonvolat\$4 adj3 (memory cell)) with first with second with (field adj effect adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 10:50
L5	11	3 and ((nonvolat\$4 adj3 (memory cell)) with (first or second) with (field adj effect adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 10:53
L6	0	3 and ((nonvolat\$4 adj3 (memory cell)) with first with other with (field adj effect adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 10:50
L7	10	3 and ((nonvolat\$4 adj3 (memory cell)) with (first other) with (field adj effect adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 10:50
L8	55	3 and ((nonvolat\$4 adj3 (memory cell)) with (field adj effect adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 10:54
L9	13	3 and ((nonvolat\$4 adj3 (memory cell)) with (field adj effect adj transistor) with (gate adj electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 10:54